Characteristic	Symbol	Min	Тур	Max	Unit
Off Characteristics					
Drain-Source Breakdown Voltage $(V_{GS} = 0 \text{ Vdc}, I_D = 100 \mu\text{A})$	V _{(BR)DSS}	65	_	_	Vdc
Zero Gate Voltage Drain Current (V _{DS} = 28 Vdc, V _{GS} = 0 Vdc)	I _{DSS}			10	μAdc
Gate - Source Leakage Current (V _{GS} = 5 Vdc, V _{DS} = 0 Vdc)	I _{GSS}	—	_	1	μAdc
On Characteristics				•	
Forward Transconductance (V _{DS} = 10 Vdc, I _D = 3 Adc)	9fs	—	7.2	_	S
Gate Threshold Voltage (V _{DS} = 10 Vdc, I _D = 300 μAdc)	VGS _(th)	2.0	-	4.0	Vdc
Gate Quiescent Voltage (V _{DS} = 26 Vdc, I _D = 750 mAdc)	V _{GS(Q)}	2.5	3.8	4.5	Vdc
Drain-Source On-Voltage (V _{GS} = 10 Vdc, I _D = 1 Adc)	V _{DS(on)}	_	0.10	—	Vdc
Dynamic Characteristics					
Reverse Transfer Capacitance ⁽¹⁾ ($V_{DS} = 26$ Vdc, $V_{GS} = 0$, f = 1 MHz)	C _{rss}	—	4.2		pF
Functional Tests (In Freescale Test Fixture)	· · · ·				
Two-Tone Common-Source Amplifier Power Gain (V_{DD} = 26 Vdc, P _{out} = 90 W PEP, I _{DQ} = 750 mA, f = 1930 MHz, Tone Spacing = 100 kHz)	G _{ps}	10	11.5	_	dB
Two-Tone Drain Efficiency (V _{DD} = 26 Vdc, P _{out} = 90 W PEP, I _{DQ} = 750 mA, f = 1930 MHz, Tone Spacing = 100 kHz)	η	33	35	_	%
3rd Order Intermodulation Distortion ($V_{DD} = 26$ Vdc, $P_{out} = 90$ W PEP, $I_{DQ} = 750$ mA, f = 1930 MHz, Tone Spacing = 100 kHz)	IMD		-30	-28	dBc
Input Return Loss (V _{DD} = 26 Vdc, P _{out} = 90 W PEP, I _{DQ} = 750 mA, f = 1930 MHz, Tone Spacing = 100 kHz)	IRL		-12	-	dB
P _{out} , 1 dB Compression Point (V _{DD} = 26 Vdc, P _{out} = 90 W CW, f = 1930 MHz)	P1dB	_	90	_	W

Table 4. Electrical Characteristics ($T_{\rm C}$ = 25°C unless otherwise noted)

1. Part is internally matched both on input and output.





V _{BIAS} B1 + $\rightarrow \bigcirc$ \bigcirc \downarrow	$ \begin{array}{c} $	$ \begin{array}{c} B2 \\ $
RF $INPUT Z1 Z2 Z3 Z4 Z5$ $C1 Z4 Z5$ $R2$ RF RF RF RF RF RF RF RF		$ \begin{array}{c} $

	2 Ferrite Beads, Round, Ferroxcube #56-590-65-3B	L1, L2	8 Turns, #26 AWG, 0.085" OD, 0.330
	Ferrite Beads, Surface Mount, Fair-Rite 2743019447		Long, Copper Wire
	0.4 - 2.5 pF Variable Capacitors, Johanson Gigatrim #27280	R1, R2	270 Ω, 1/4 W Chip Resistors, Garrett
3	10 pF Chip Capacitors, ATC #100B100CT500XT		Instruments #RM73B2B271JT
	12 pF Chip Capacitor, ATC #100B120CT500XT	Z1	ZO = 50 Ohms
	0.3 pF Chip Capacitor, ATC #100B0R3CT500XT	Z2	ZO = 50 Ohms, Lambda = 0.123
	120 pF Chip Capacitors, ATC #100B12R1CT500XT	Z3	ZO = 15.24 Ohms, Lambda = 0.0762
	0.1 μF Chip Capacitors, Kemet #CDR33BX104AKYS	Z4	ZO = 10.11 Ohms, Lambda = 0.0392
	1000 pF Chip Capacitors, ATC #100B102JT50XT	Z5	ZO = 6.34 Ohms, Lambda = 0.0711
	22 μF, 35 V Tantalum Chip Capacitors,	Z6	ZO = 5.02 Ohms, Lambda = 0.0476
	Kemet #T491X226K035AT	Z7	ZO = 5.54 Ohms, Lambda = 0.0972
	10 μF, 35 V Tantalum Chip Capacitors,	Z8	ZO = 50.0 Ohms, Lambda = 0.194
	Kemet #T495X106K035AT	Z9	ZO = 50.0 Ohms
	1 μF, 35 V Tantalum Chip Capacitors,	Raw PCB Material	0.030" Glass Teflon [®] , ε_r = 2.55,
	Kemet #T495X105K035AT		2 oz Copper, 3″ x 5″ Dimensions

Figure 1. MRF19090 Test Circuit Schematic

RF Device Data Freescale Semiconductor



Freescale has begun the transition of marking Printed Circuit Boards (PCBs) with the Freescale Semiconductor signature/logo. PCBs may have either Motorola or Freescale markings during the transition period. These changes will have no impact on form, fit or function of the current product.

Figure 2. MRF19090 Test Circuit Component Layout

MAY

LAS

-AST ORDER 3 OCT 08

TYPICAL CHARACTERISTICS



and Gain versus Supply Voltage

MRF19090SR3



 V_{DD} = 26 V, I_{DQ} = 750 mA, P_{out} = 90 Watts (PEP)

f MHz	Z_{source}	Z_{load}
1930	4.5 - j6.1	1.1 - j4.5
1960	4.4 - j6.0	1.1 - j4.4
1990	4.3 - j6.1	1.1 - j4.3

Z_{source} = Test circuit impedance as measured from gate to ground.

Z_{load} = Test circuit impedance as measured from drain to ground.





PACKAGE DIMENSIONS





CASE 465C-02 **ISSUE D** NI-880S MRF19090SR3

NOTES: 1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M-1994. 2. CONTROLLING DIMENSION: INCH. 3. DIMENSION H IS MEASURED 0.030 (0.762) AWAY FROM PACKAGE BODY.

	INCHES		MILLIMETERS		
DIM	MIN	MAX	MIN	MAX	
Α	0.905	0.915	22.99	23.24	
В	0.535	0.545	13.60	13.80	
C	0.147	0.200	3.73	5.08	
D	0.495	0.505	12.57	12.83	
Е	0.035	0.045	0.89	1.14	
F	0.003	0.006	0.08	0.15	
Н	0.057	0.067	1.45	1.70	
K	0.170	0.210	4.32	5.33	
Μ	0.872	0.888	22.15	22.55	
Ν	0.871	0.889	19.30	22.60	
R	0.515	0.525	13.10	13.30	
S	0.515	0.525	13.10	13.30	
aaa	0.007	0.178 REF 0.178 REF			
bbb	0.010) REF	0.254 REF		
CCC	0.015	015 BEF 0.381 BEF			

STYLE 1: PIN 1. DRAIN 2. GATE 3. SOURCE

PRODUCT DOCUMENTATION

Refer to the following documents to aid your design process.

Engineering Bulletins

• EB212: Using Data Sheet Impedances for RF LDMOS Devices

REVISION HISTORY

The following table summarizes revisions to this document.

Revision	Date	Description
8	Oct. 2008	 Data sheet revised to reflect part status change, p. 1, including use of applicable overlay. Modified data sheet to reflect RF Test Reduction described in Product and Process Change Notification number, PCN12779, p. 1, 2 Updated Part Numbers in Figure 1, Test Circuit Schematic, to RoHS compliant part numbers, p. 3 Added Product Documentation and Revision History, p. 8

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